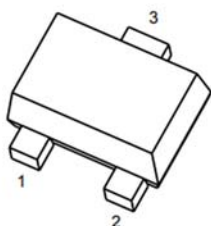
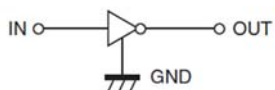
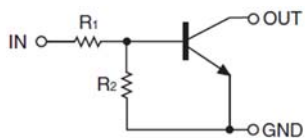


NPN Digital Transistors (Built-in Resistors)



1. IN
2. GND
3. OUT

SOT-723

Features

- Moisture sensitivity level 1
- Halogen free and RoHS compliant
- Surface mount package ideally suited for automatic insertion

Application

- Signal amplification
- Switching circuit

Mechanical data

- **Package:** SOT-723
- **Terminals:** Tin plated leads, solderable per J-STD-002 and JESD22-B102

■ Maximum Ratings ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Conditions	Value
Device marking code				29
Supply voltage	V_{CC}	V		50
Input voltage	V_{IN}	V		-10 to +40
Output current	I_O	mA		100
Power dissipation	P_D	mW		100
Junction temperature	T_J	$^{\circ}\text{C}$		-55 to +150
Storage temperature	T_{STG}	$^{\circ}\text{C}$		-55 to +150



DTC115EM

■ Electrical Characteristics (T_a=25°C Unless otherwise specified)

Item	Symbol	Unit	Conditions	Min	Typ	Max
Input voltage	V _{I(off)}	V	V _{CC} =5V, I _O =100uA	0.5		
	V _{I(on)}	V	V _O =0.3V, I _O =1mA			3.0
Output voltage	V _{O(on)}	V	I _O / I _I =5mA/0.25 mA			0.3
Input current	I _I	mA	V _I =5V			3.6
Output current	I _{O(off)}	uA	V _{CC} =50V, V _I =0			0.1
DC current gain	G _I		V _O =5V, I _O =5mA	82		
Input resistance	R ₁	kΩ		70	100	130
Resistance ratio	R ₂ /R ₁			0.8	1	1.2
Transition frequency	f _T	MHz	V _O =10V, I _O =-5mA, f=100MHz		250	

■ Thermal Characteristics

Parameter	Symbol	Unit	Value
Thermal resistance, junction-to-ambient	R _{θJ-A} ⁽¹⁾	°C/W	1250
Thermal resistance, junction-to-case	R _{θJ-C} ⁽¹⁾	°C/W	1000

Note:

(1) Thermal resistance from junction to ambient and from junction to case mounted on P.C.B. with 25.4mm*25.4mm copper pad areas

■ Ordering Information

Preferred P/N	Packing code	Unit weight(g)	Minimum package(pcs)	Inner box quantity(pcs)	Outer carton quantity(pcs)	Delivery mode
DTC115EM	F2	Approximate 0.0013	8000	80000	320000	7" reel



■Characteristics(Typical)

Fig. 1 - DC Current Gain Characteristics

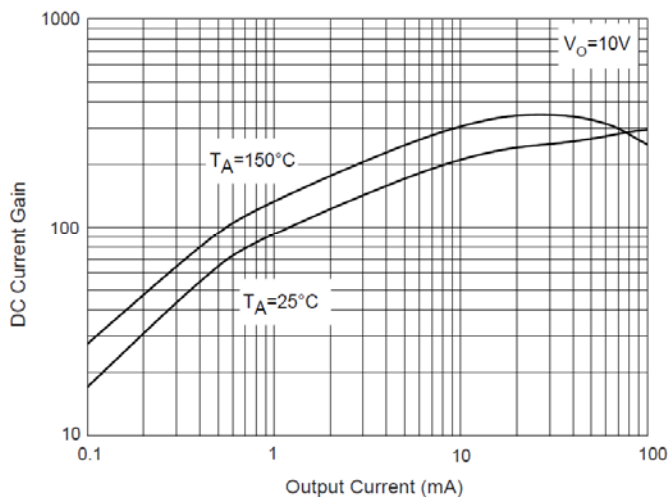


Fig. 2 - Input Voltage (on) Characteristics

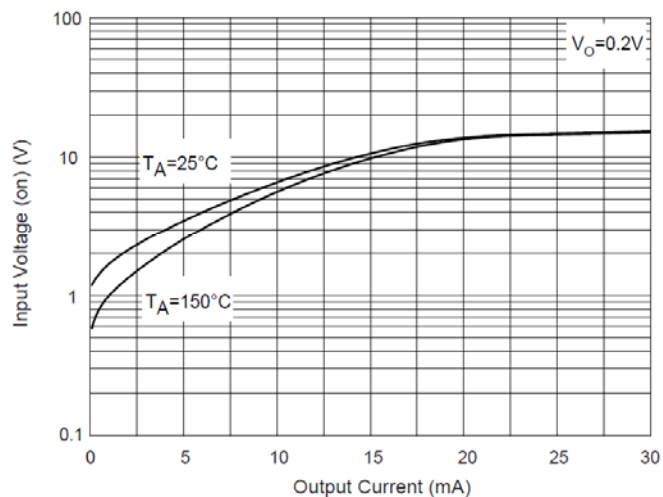


Fig. 3 - Input Voltage (on) Characteristics

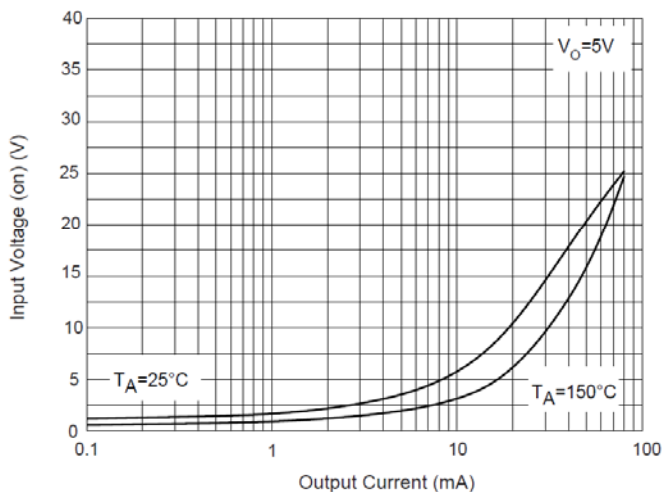


Fig. 4 - Collector-Emitter Saturation Voltage Characteristics

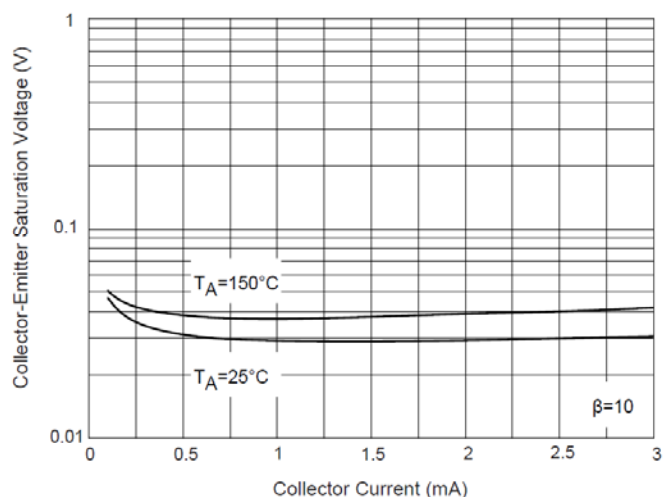
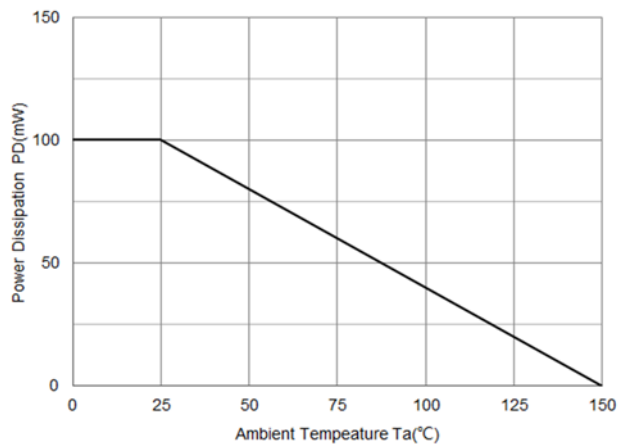


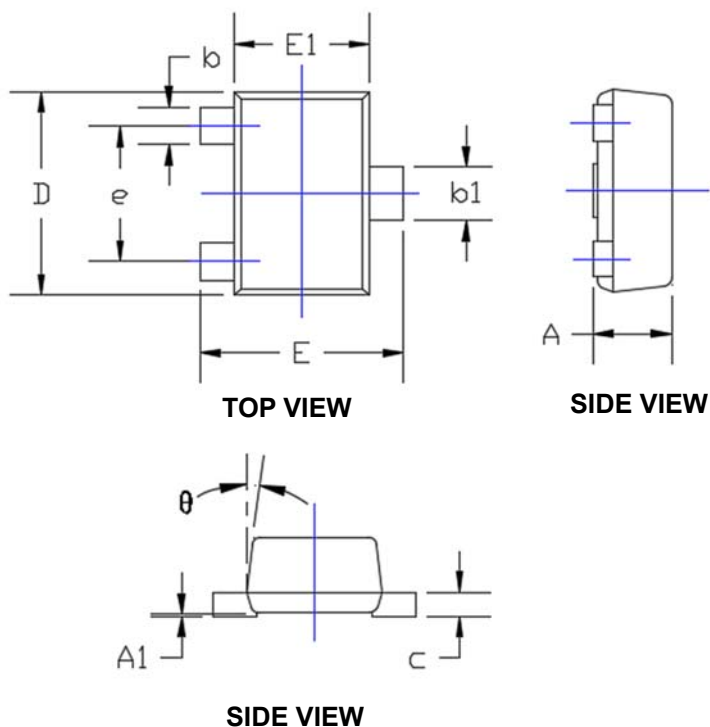
Fig5. P_D ----- T_A





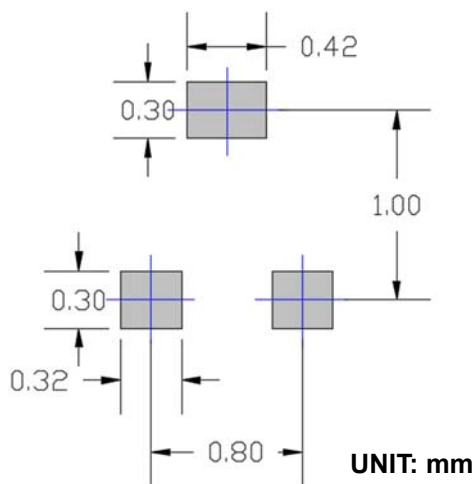
DTC115EM

■ Outline Dimensions



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.017	0.022	0.430	0.550
A1	0.000	0.002	0.000	0.050
b	0.007	0.011	0.170	0.270
b1	0.011	0.015	0.270	0.370
c	0.003	0.008	0.080	0.200
D	0.045	0.049	1.150	1.250
E	0.045	0.049	1.150	1.250
E1	0.030	0.033	0.750	0.850
e	0.031TYP.		0.800TYP.	
θ	7°REF.		7°REF.	

■ Suggested Pad Layout





DTC115EM

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